



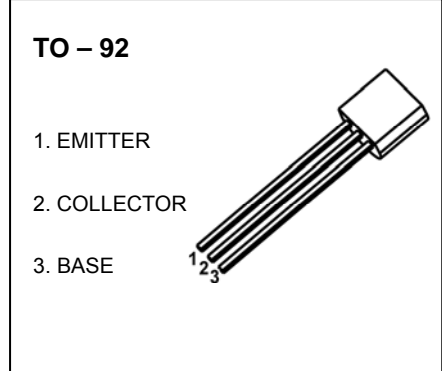
**2SC536** TRANSISTOR (NPN)

**FEATURES**

- General Purpose Amplifier Transistor

**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	40	V
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current	0.1	A
P <sub>C</sub>	Collector Power Dissipation	0.4	W
R <sub>θJA</sub>	Thermal Resistance From Junction To Ambient	312	°C/W
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	°C



**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 0.1mA, I <sub>E</sub> =0	40			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =1mA, I <sub>B</sub> =0	30			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =0.1mA, I <sub>C</sub> =0	5			V
Collector cut-off current	I <sub>CB0</sub>	V <sub>CB</sub> =35V, I <sub>E</sub> =0			1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =4V, I <sub>C</sub> =0			1	μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA	60		960	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA			0.5	V
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =6V, f=1MHz		3.5		pF
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA		100		MHz

**CLASSIFICATION OF h<sub>FE</sub>**

RANK	D	E	F	G	H
RANGE	60-120	100-200	160-320	280-560	480-960